Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claim 1 (Currently Amended): A gauge apparatus for use in a semiconductor fabrication system, said apparatus comprising:

an electrostatic chuck associated with a semiconductor fabrication system, wherein said electrostatic chuck is moveable from a first horizontal position to a second horizontal position and moveable from a first vertical position to a second vertical position; and

a gauge for measuring a gap between a baffle plate and a chamber wall in order to thereby prevent damage to said chamber wall by said baffle plate during a movement of said electrostatic chuck during a semiconductor fabrication operation of said semiconductor fabrication system, wherein said gauge is located proximate to said electrostatic chuck at said second position of said electrostatic chuck, said gauge comprising:

a leveling mechanism for measuring a horizontal gap between said baffle plate and said chamber wall, the leveling mechanism disposed between said electrostatic chuck at said second position of said electrostatic chuck and said chamber wall; and

a modified portion mechanically associated with the leveling mechanism.

Claim 2 (Original): The apparatus of Claim 1, wherein said semiconductor fabrication operation comprises a wet cleaning semiconductor operation.

Claim 3 (Original): The apparatus of Claim 1, wherein said gauge is adapted for use in leveling said electrostatic chuck.

Claim 4 (Original): The apparatus of Claim 1, wherein said gauge comprises a horizontal gap gauge.

Claim 5 (Original): The apparatus of Claim 1, wherein said gauge is adapted for use in preventing polymer peeling of said chamber wall.

Claim 6 (Canceled)

Claim 7 (Original): The apparatus of Claim 1, wherein said semiconductor fabrication system comprises dual-rotate-magnet (DRM).

Claim 8 (Original): The apparatus of claim 7 wherein said semiconductor fabrication system comprises a focus ring.

Claim 9 (Previously Presented): The apparatus of Claim 8, wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.

Claim 10 (Previously Presented): The apparatus of Claim 8, wherein said movement of said electrostatic chuck during said semiconductor fabrication operations comprises a horizontal movement.

Claim 11 (Currently Amended): A method for preventing damage to a chamber wall by a baffle plate in a semiconductor fabrication system during a semiconductor fabrication operation, said method comprising the steps of:

moving an electrostatic chuck associated with said semiconductor fabrication system during said semiconductor fabrication operation; and

measuring at least one element selected from a group consisting essentially of a horizontal gap and a vertical gap between said baffle plate and said chamber wall utilizing a gauge having a leveling mechanism and a modified portion, said

gauge integrated with said semiconductor fabrication system, in response to moving said electrostatic chuck to thereby prevent damage to said chamber wall by said baffle plate.

Claim 12 (Original): The method of Claim 11 wherein said semiconductor fabrication operation comprises a wet cleaning semiconductor operation.

Claim 13 (Previously Presented): The method of Claim 11 wherein said gauge is adapted for use in leveling said electrostatic chuck.

Claim 14 (Original): The method of Claim 11 wherein said gauge comprises a horizontal gap gauge.

Claim 15 (Original): The method of Claim 11 wherein said gauge is adapted for use in preventing polymer peeling of said chamber wall.

Claim 16 (Canceled)

Claim 17 (Original): The method of Claim 11 wherein said semiconductor fabrication system comprises dual-rotate-magnet (DRM).

Claim 18 (Original): The method of Claim 17 wherein said semiconductor fabrication system comprises a focus ring.

Claim 19 (Previously Presented): The method of Claim 18 wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.

Claim 20 (Previously Presented): The method of Claim 18 wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a horizontal movement.

Claim 21 (Currently Amended): A gauge apparatus for use in a semiconductor fabrication system, said apparatus comprising:

an electrostatic chuck associated with a semiconductor fabrication system comprising a dual-rotate-magnet (DRM) and a focus ring, wherein said electrostatic chuck is moveable from a first position to a second position; and

a horizontal gap gauge for accurately measuring a horizontal gap between a baffle plate and a chamber wall, and preventing polymer peeling of said chamber wall by said baffle plate during a movement of said electrostatic chuck during semiconductor fabrication operation of said semiconductor fabrication system in order to assist in leveling said electrostatic chuck, wherein said gauge is located proximate to said electrostatic chuck at said second position of said electrostatic chuck, wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.

Claim 22 (Currently Amended): A method for preventing damage to a chamber wall by a baffle plate in a semiconductor fabrication system during a semiconductor fabrication operation, said method comprising the steps of:

associating an electrostatic chuck with a semiconductor fabrication system comprising a dual-rotate-magnet (DRM) and a focus ring, wherein said electrostatic chuck is moveable from a first position to a second position; and

utilizing a leveling to measure a horizontal gap between formed between a baffle plate and a chamber wall and preventing damage to said chamber wall by said baffle plate during a movement of said electrostatic chuck during a semiconductor fabrication operation of said semiconductor fabrication system utilizing a gauge that is located proximate to said electrostatic chuck, wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.